

2SK2553(L), 2SK2553(S)

Silicon N Channel MOS FET
High Speed Power Switching

REJ03G1015-1000
(Previous: ADE-208-357H)
Rev.10.00
Sep 07, 2005

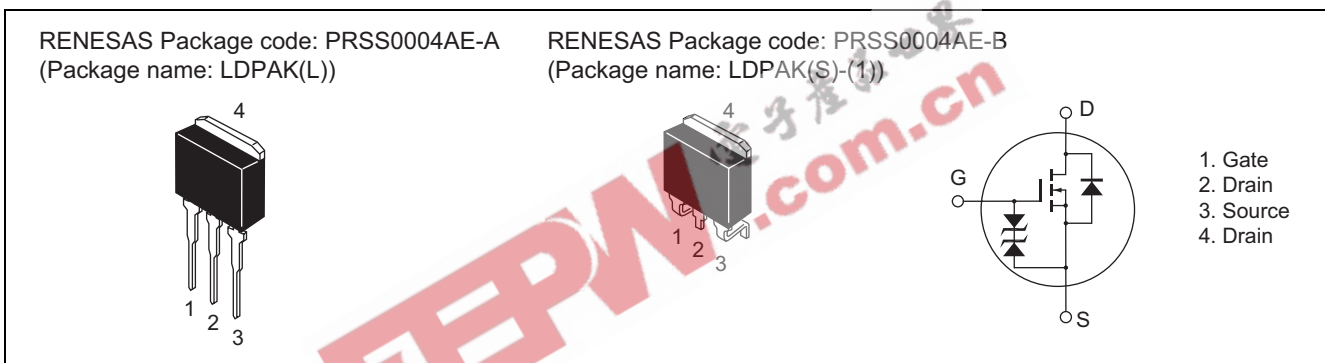
Application

High speed power switching

Features

- Low on-resistance
- $R_{DS(on)} = 7 \text{ m}\Omega$ typ.
- High speed switching
- 4 V gate drive device can be driven from 5 V source

Outline



Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	60	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	50	A
Drain peak current	I _{D(pulse)} ^{Note 1}	200	A
Body to drain diode reverse drain current	I _{DR}	50	A
Avalanche current	I _{AP} ^{Note 3}	45	A
Avalanche energy	E _{AR} ^{Note 3}	174	mJ
Channel dissipation	P _{ch} ^{Note 2}	75	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1 %
 2. Value at T_c = 25°C
 3. Value at T_{ch} = 25°C, R_g ≥ 50 Ω

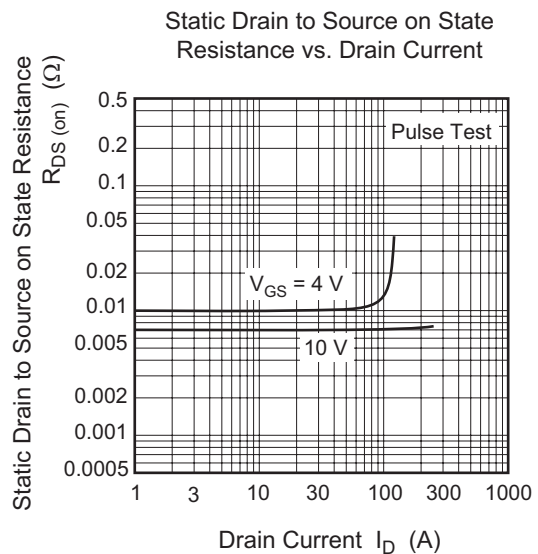
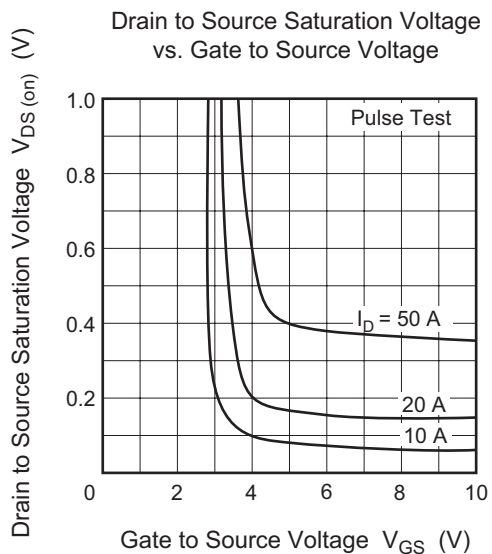
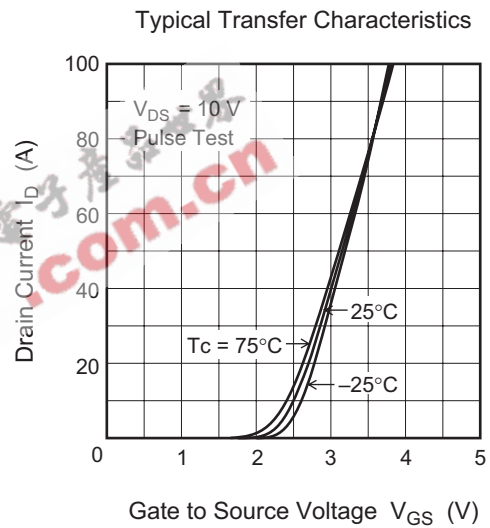
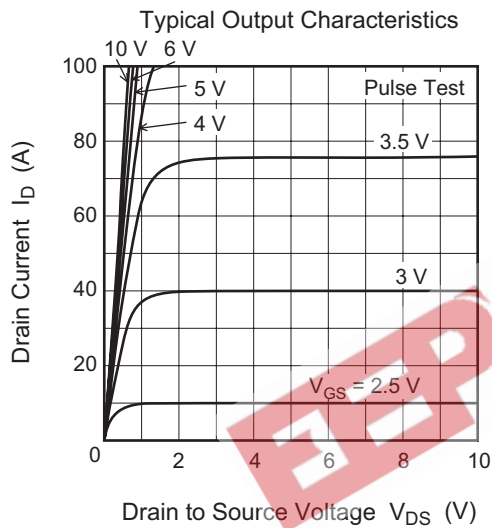
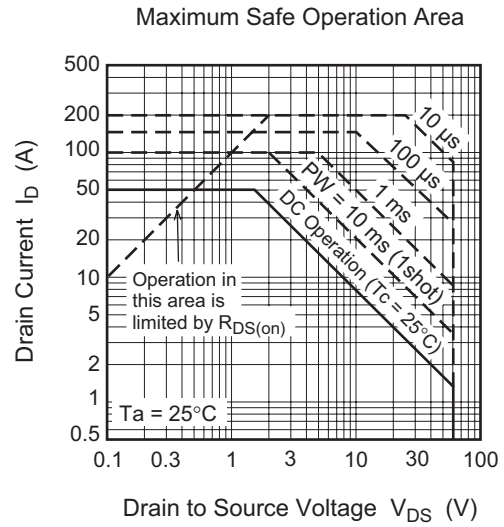
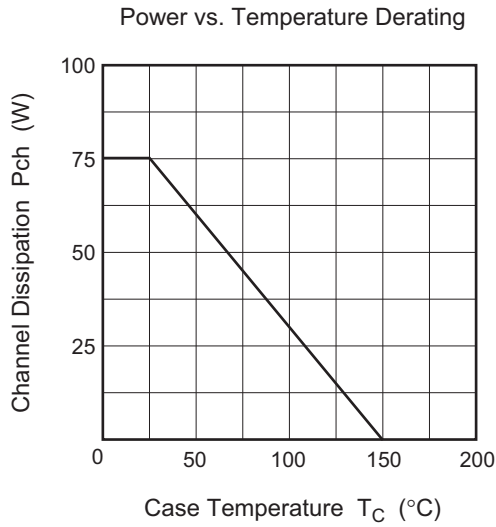
Electrical Characteristics

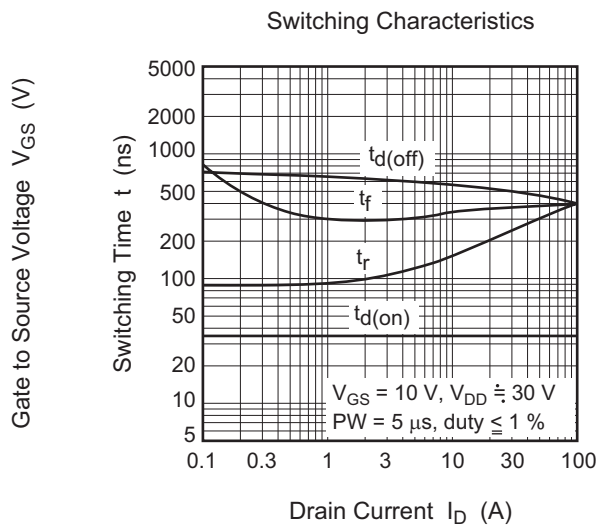
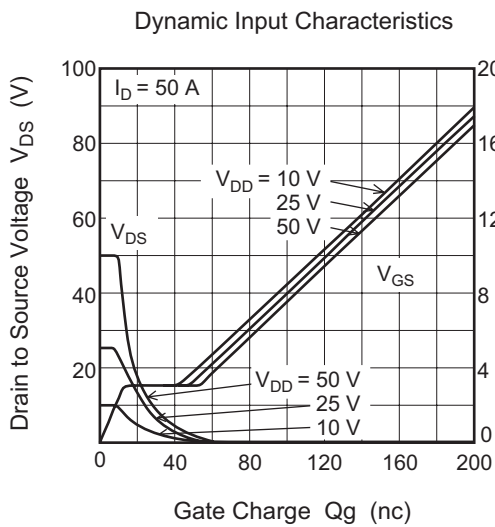
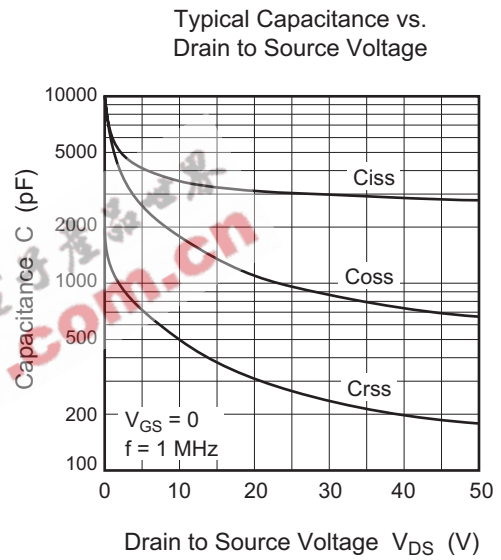
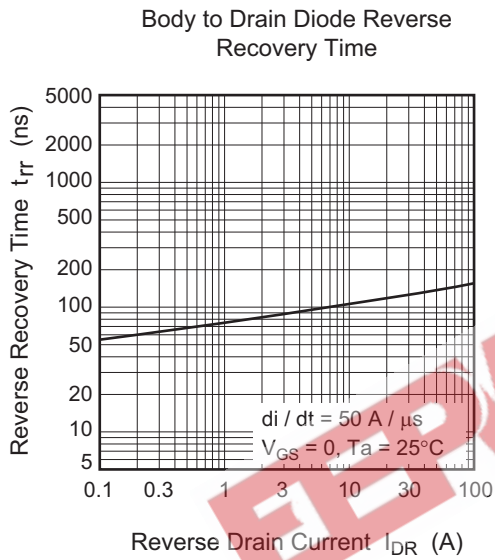
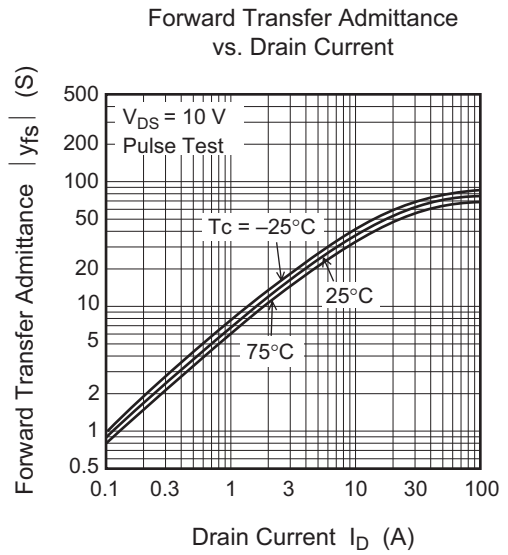
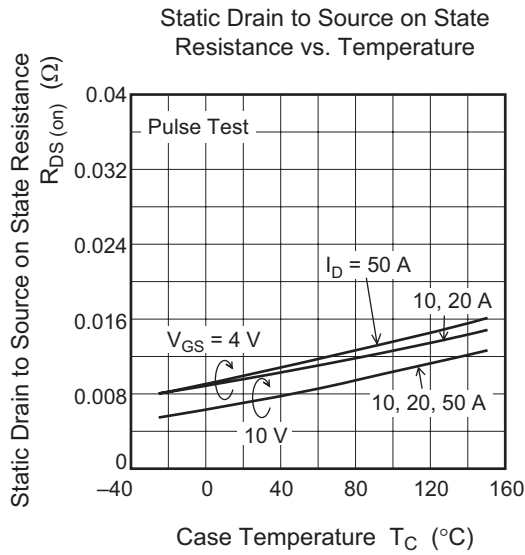
(Ta = 25°C)

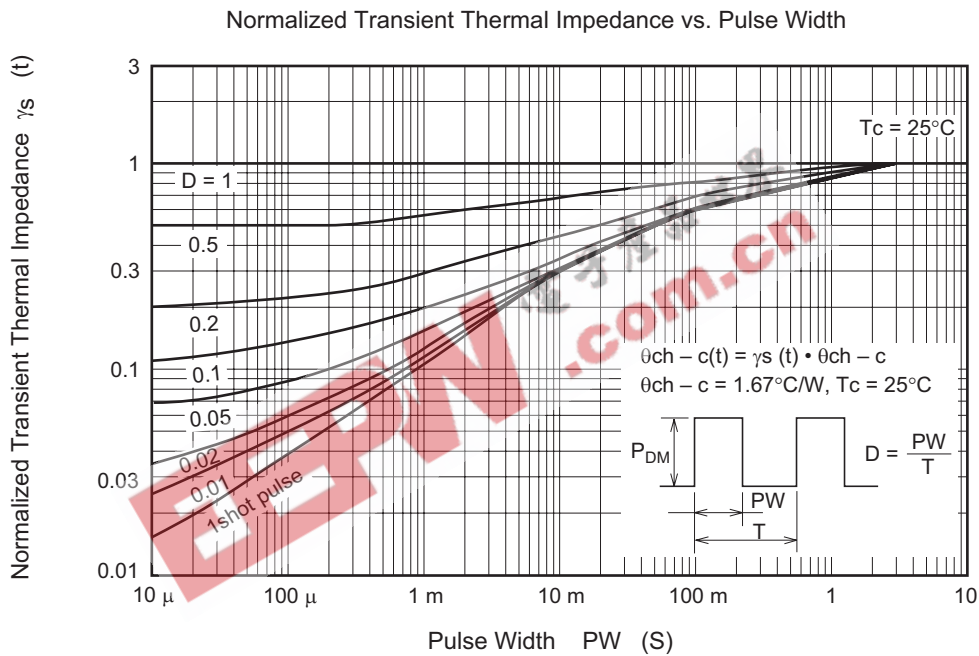
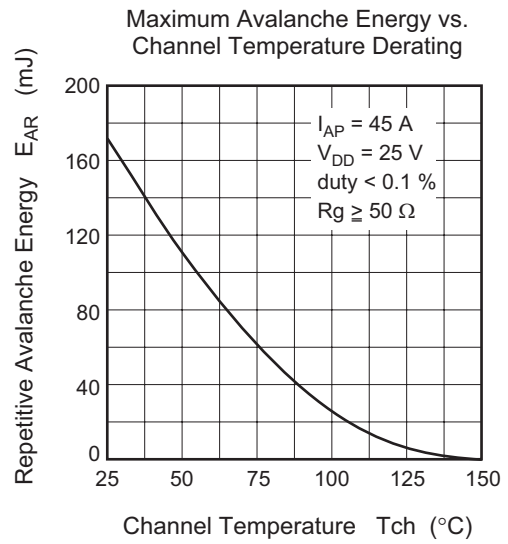
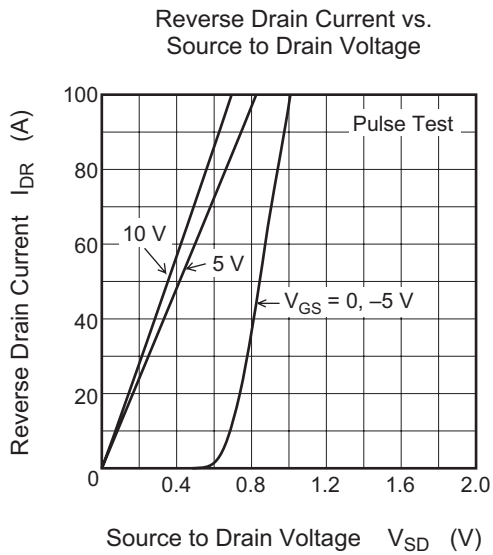
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	V _{(BR)DSS}	60	—	—	V	I _D = 10 mA, V _{GS} = 0
Gate to source breakdown voltage	V _{(BR)GSS}	±20	—	—	V	I _G = ±100 μA, V _{DS} = 0
Gate to source leak current	I _{GSS}	—	—	±10	μA	V _{GS} = ±16 V, V _{DS} = 0
Zero gate voltage drain current	I _{DSS}	—	—	10	μA	V _{DS} = 60 V, V _{GS} = 0
Gate to source cutoff voltage	V _{GS(off)}	1.0	—	2.0	V	I _D = 1 mA, V _{DS} = 10 V
Static drain to source on state resistance	R _{DS(on)}	—	7	10	mΩ	I _D = 25 A, V _{GS} = 10 V ^{Note 4}
		—	10	16	mΩ	I _D = 25 A, V _{GS} = 4 V ^{Note 4}
Forward transfer admittance	y _{fs}	35	55	—	S	I _D = 25 A, V _{DS} = 10 V ^{Note 4}
Input capacitance	C _{iss}	—	3550	—	pF	V _{DS} = 10 V, V _{GS} = 0, f = 1 MHz
Output capacitance	C _{oss}	—	1760	—	pF	
Reverse transfer capacitance	C _{rss}	—	500	—	pF	
Turn-on delay time	t _{d(on)}	—	35	—	ns	I _D = 25 A, V _{GS} = 10 V, R _L = 1.2 Ω
Rise time	t _r	—	230	—	ns	
Turn-off delay time	t _{d(off)}	—	470	—	ns	
Fall time	t _f	—	360	—	ns	
Body to drain diode forward voltage	V _{DF}	—	0.85	—	V	I _F = 50 A, V _{GS} = 0
Body to drain diode reverse recovery time	t _{rr}	—	135	—	ns	I _F = 50 A, V _{GS} = 0 di _F / dt = 50 A / μs

Note: 4. Pulse Test

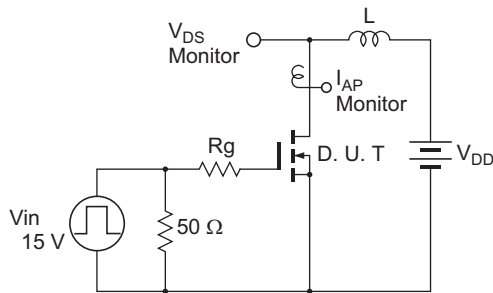
Main Characteristics



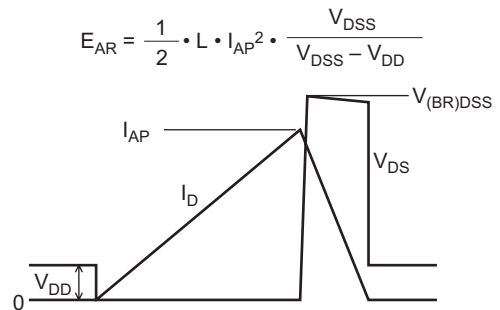


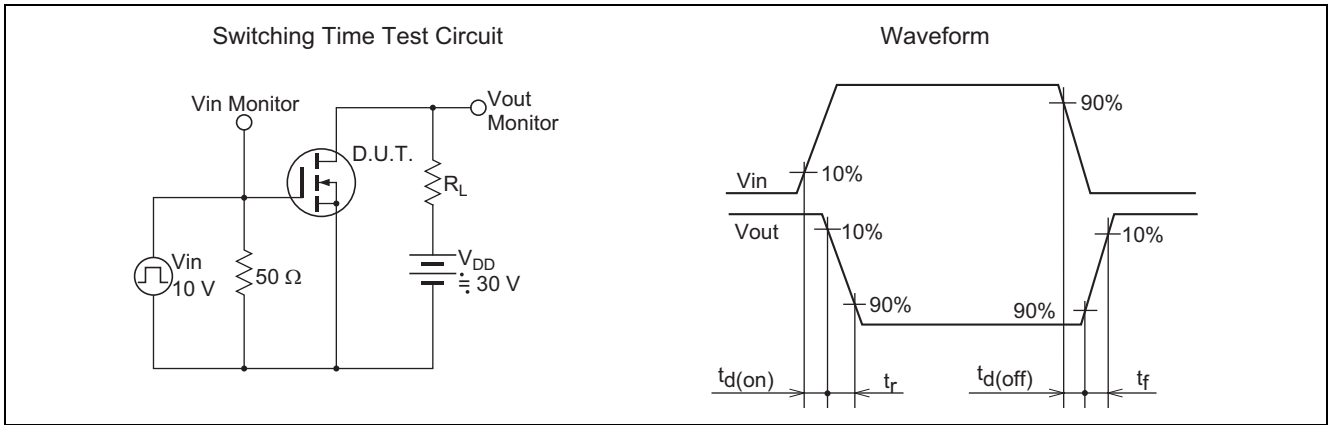


Avalanche Test Circuit



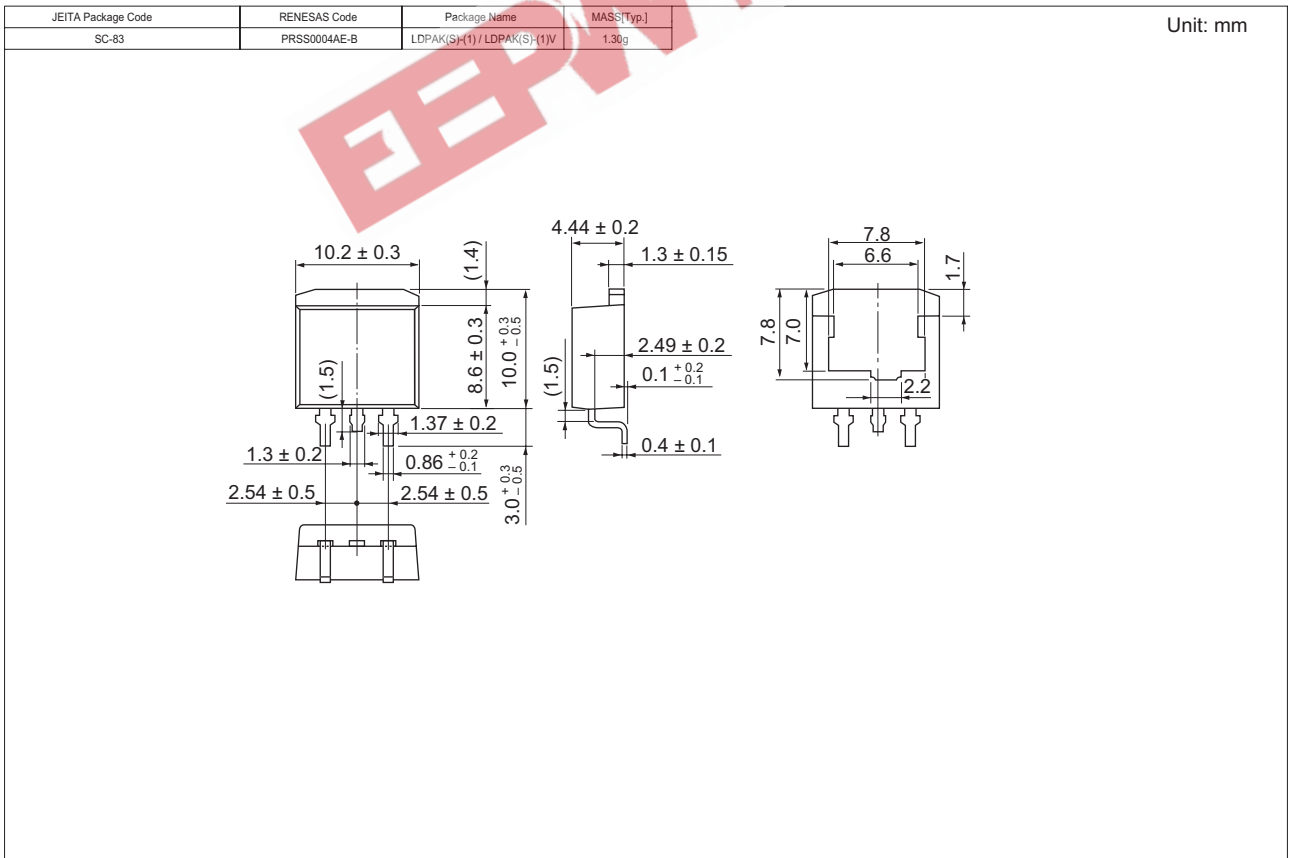
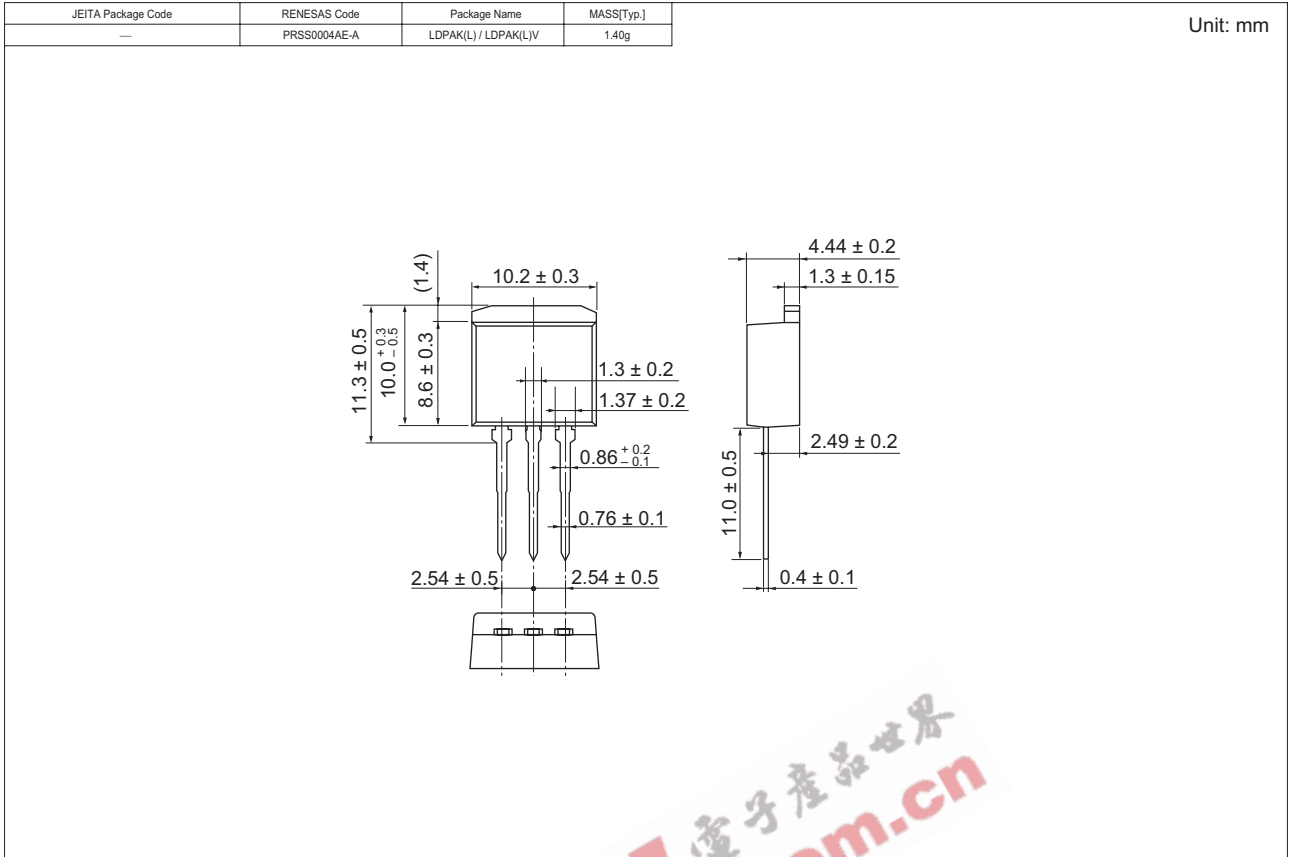
Avalanche Waveform





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Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SK2553L-E	500 pcs	Box (Sack)
2SK2553STL-E	1000 pcs	Taping

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Renesas Technology Malaysia Sdn. Bhd.

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